



DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)}	I _D T _A = 25°C
-20V	$5.5\Omega @ V_{GS} = -4.5V$	-200mA
	7.5Ω @ V _{GS} = -2.5V	-170mA

Description and Applications

This new generation MOSFET has been designed to minimize the onstate resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Power management functions

Features and Benefits

- Dual P-Channel MOSFET
- Low On-Resistance
 - 5.5Ω @ -4.5V
 - 7.5Ω @ -2.5V
 - 11.5Ω @ -1.8V
 17.5Ω @ -1.5V
- Very Low Gate Threshold Voltage V_{GS(TH)} <1.15V
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green" Device (Note 2)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

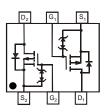
- Case: SOT-963
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper lead frame. Solderable per MIL-STD-202, Method 208
- Weight: 0.0027 grams (approximate)





SOT-963

Top View



Internal Schematic

Ordering Information (Note 3)

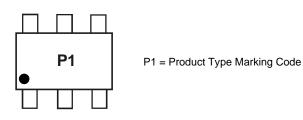
Part Number	Case	Packaging
DMP210DUDJ-7	SOT-963	10,000/Tape & Reel

Notes: 1. No purposefully added lead.

2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.

3. For packaging details, go to our website at http://www.diodes.com.

Marking Information (Note 4)



Notes: 4. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		VDSS	-20	V
Gate-Source Voltage		V _{GSS}	±8	V
Continuous Drain Current (Note 5) V_{GS} = -4.5V	T _A = 25°C T _A = 70°C	ID	-200 -150	mA
Continuous Drain Current (Note 5) V_{GS} = -2.5V	T _A = 25°C T _A = 70°C	I _D	-170 -130	mA
Pulsed Drain Current	T _P = 10μs	I _{DM}	-600	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	PD	330	mW
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	377.16	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @TA = 25°C unless otherwise specified Symbol Min Max Unit **Test Condition** Characteristic Тур **OFF CHARACTERISTICS (Note 6)** Drain-Source Breakdown Voltage -20 V **BV**_{DSS} $V_{GS} = 0V, I_D = -250 \mu A$ -100 $V_{DS} = -16V, V_{GS} = 0V$ nA Zero Gate Voltage Drain Current IDSS -50 nA $V_{DS} = -5.0V, V_{GS} = 0V$ ____ $V_{GS} = \pm 5.0V, V_{DS} = 0V$ ±100 nA Gate-Source Leakage IGSS ____ $V_{GS} = \pm 8.0V, V_{DS} = 0V$ μΑ ±1 ON CHARACTERISTICS (Note 6) Gate Threshold Voltage V V_{GS(th)} -0.45 -1.15 $V_{DS} = V_{GS}, I_D = -250 \mu A$ 5.5 $V_{GS} = -4.5V, I_D = -100mA$ 7.5 $V_{GS} = -2.5V, I_D = -50mA$ Static Drain-Source On-Resistance 11.5 V_{GS} = -1.8V, I_D = -20mA Ω R_{DS} (ON) 17.5 $V_{GS} = -1.5V, I_D = -10mA$ ____ 20 $V_{GS} = -1.2V, I_D = -10mA$ ____ ____ Forward Transfer Admittance |Y_{fs}| 150 200 mS $V_{DS} = -10V, I_D = -0.2A$ Diode Forward Voltage (Note 6) -0.5 -1.2 V $V_{GS} = 0V, I_{S} = -115mA$ VSD DYNAMIC CHARACTERISTICS (Note 7) Input Capacitance Ciss 13.72 175 pF $V_{DS} = -15V, V_{GS} = 0V$ Coss **Output Capacitance** 4.01 30 pF f = 1.0MHzReverse Transfer Capacitance 2.34 20 pF Crss SWITCHING CHARACTERISTICS (Note 7) Turn-On Delay Time 7.7 td(on) Rise Time 19.3 $V_{GS} = -4.5V, V_{DD} = -15V$ tr ____ ns Turn-Off Delay Time 25.9 I_D = -180mA, R_G = 2.0 Ω t_{d(off)} Fall Time 31.5 tf

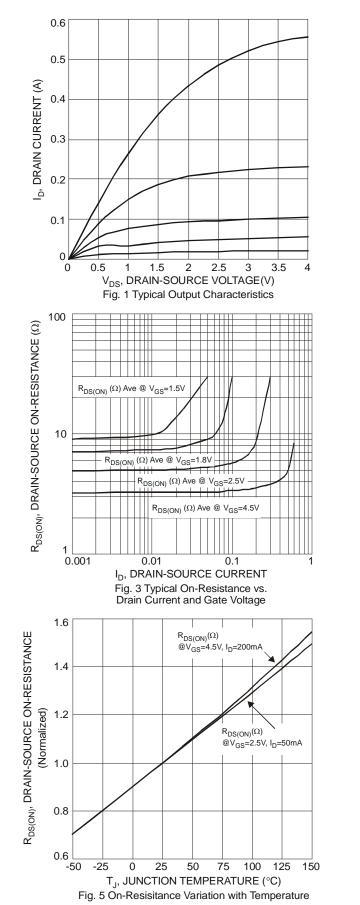
Notes: 5. Device mounted on 1"x1" FR-4 substrate PC board, with minimum recommended pad layout, single sided.

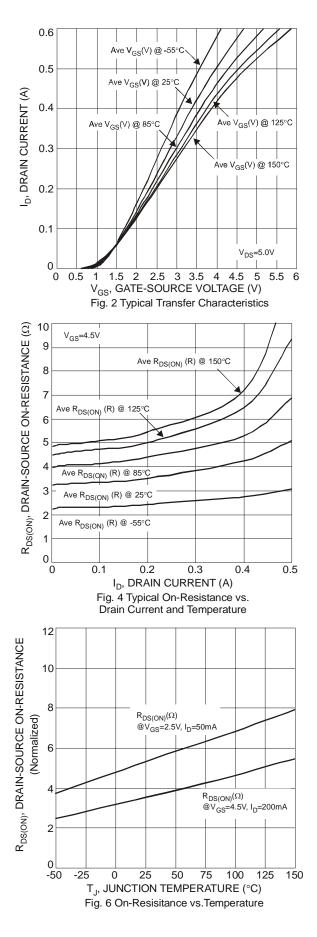
6. Short duration pulse test used to minimize self-heating effect.

7. Guaranteed by design. Not subject to production testing.

DMP210DUDJ

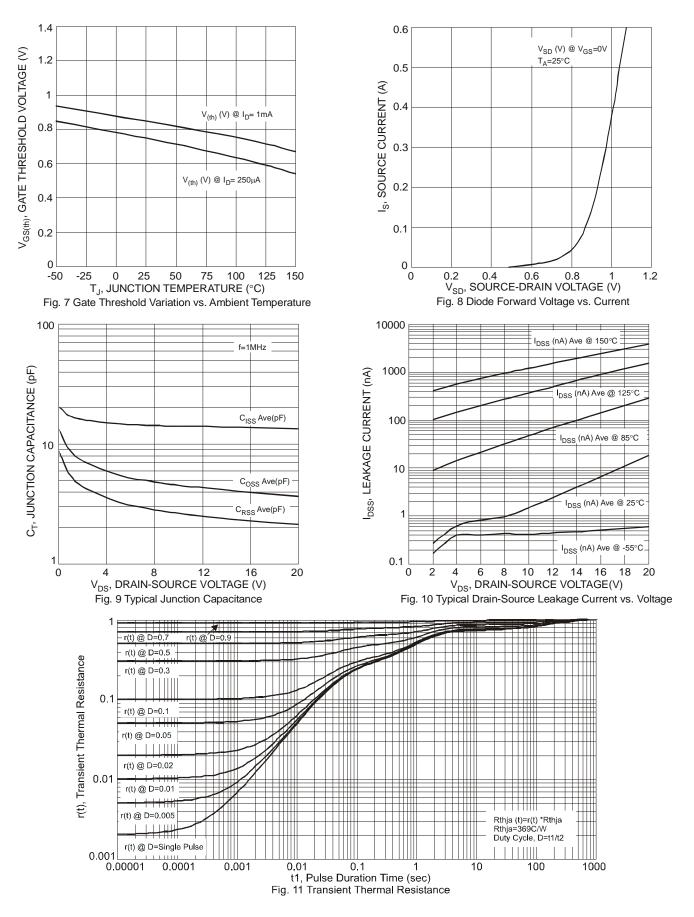






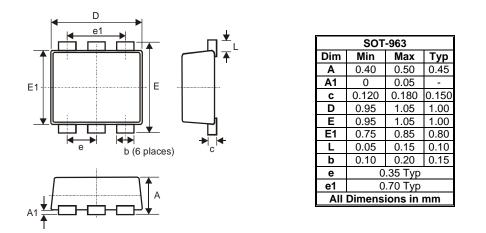
DMP210DUDJ



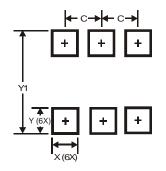




Package Outline Dimensions



Suggested Pad Layout



Dimensions	Value (in mm)
С	0.350
Х	0.200
Y	0.200
Y1	1.100



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